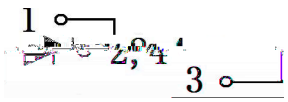
TO-263

Schottky Diode in a TO-263 Plastic Package.

High Forward Surge Capability, Ultra Low Forward Voltage Drop, Excellent High Temperature Stability.

For use in low voltage,high frequency inverters, free wheeling, and polarity protection applications.





PIN1 Anode PIN 2,4 Cathode PIN 3 Anode

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RM} V_{RSM} V_{DC}	100	V
RMS Reverse Voltage	V_{RMS}	70	V
Average forward rectified current	$I_{F(AV)}$	1×10	A
Non Repetitive Peak Surge Current	I_{FSM}	200	A
Thermal Resistance Junction to Case	$R_{\theta Jc}$	2.8	/W
Junction and Storage Temperature Range	T_j T_{stg}	-55 +150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_{(BR)R}$	I_R=1mA(Ta=25)	100			V
Forward Voltage	V_F	I_F =2A(Ta=25)		0.41	0.45	V
		I_F =10A(Ta=25)		0.58	0.65	V
		I_F =2A(Ta=125)		0.31	0.40	V
		I_F =10A(Ta=125)		0.55	0.65	V
Instantaneous Reverse Current	I_R Note 1	V_R=100V(Ta=25)			150	μA
		V_R=100V(Ta=125)			25	mA

/Notes

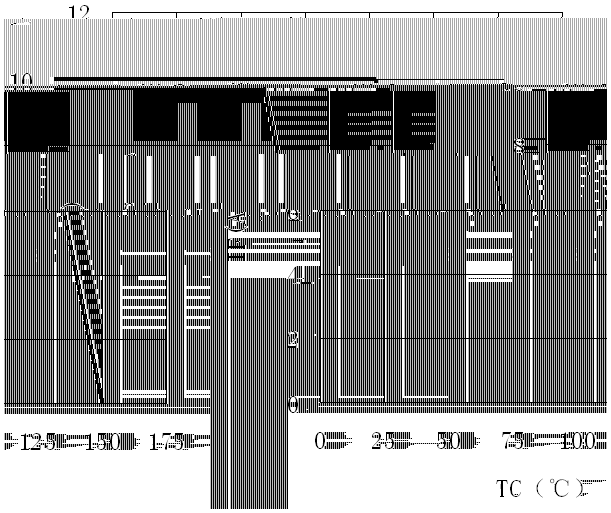
1.

Short duration pulse test used to minimize self-heating effect.

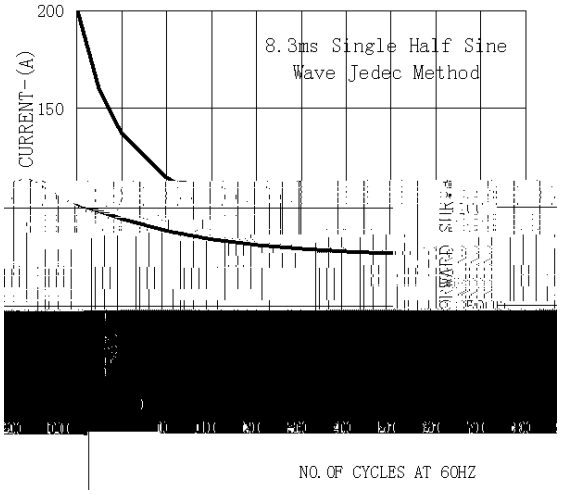
2.

Unless otherwise noted, values for the parameters of a single chip

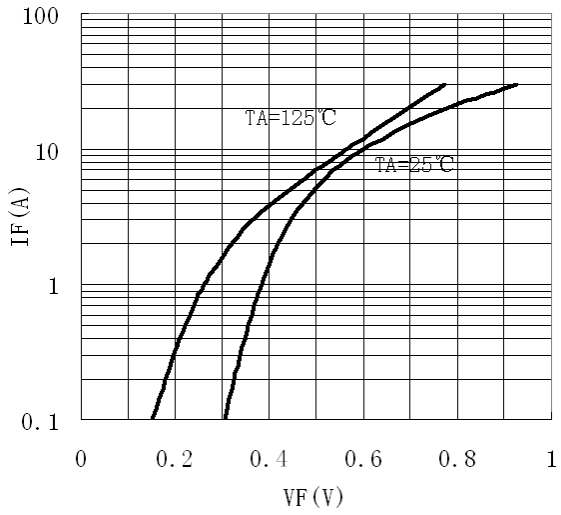
IF - TC



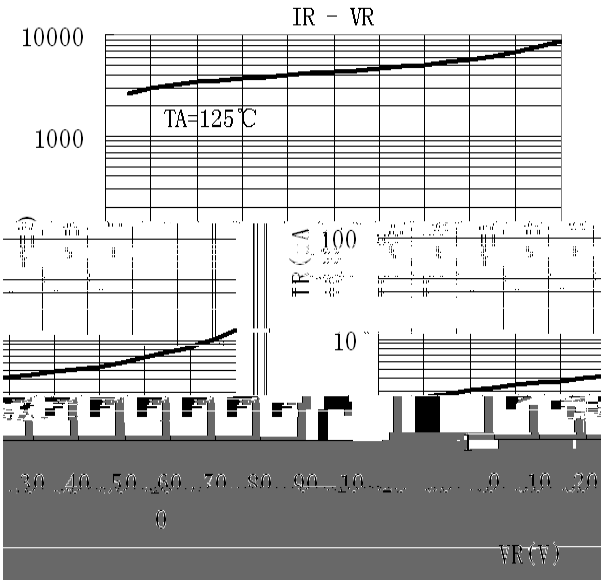
IFSM



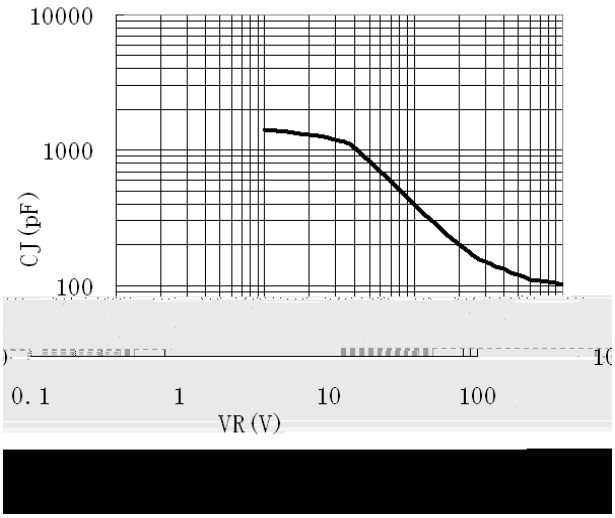
IF - VF

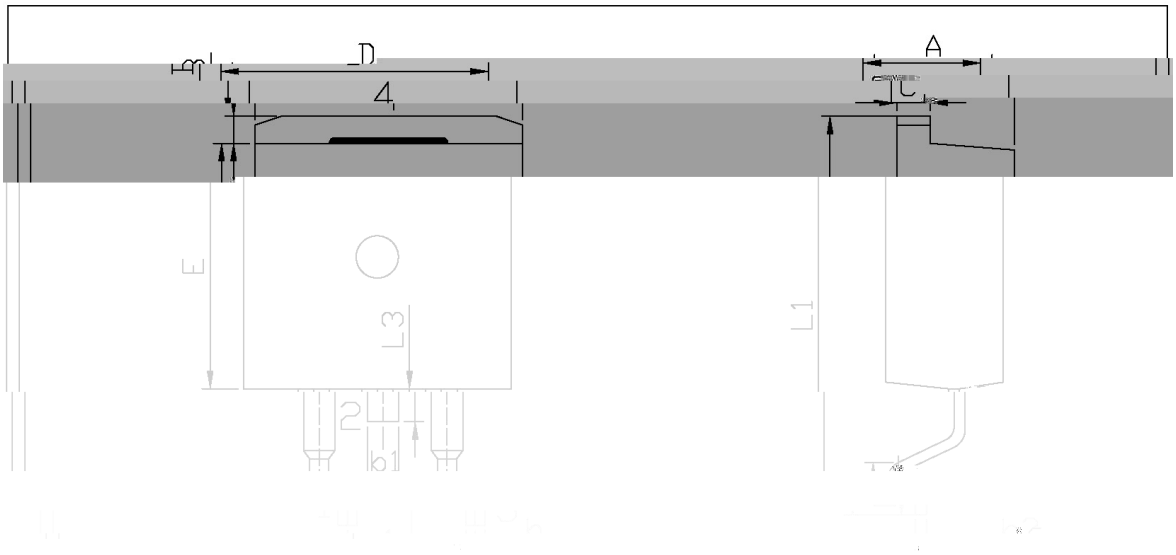


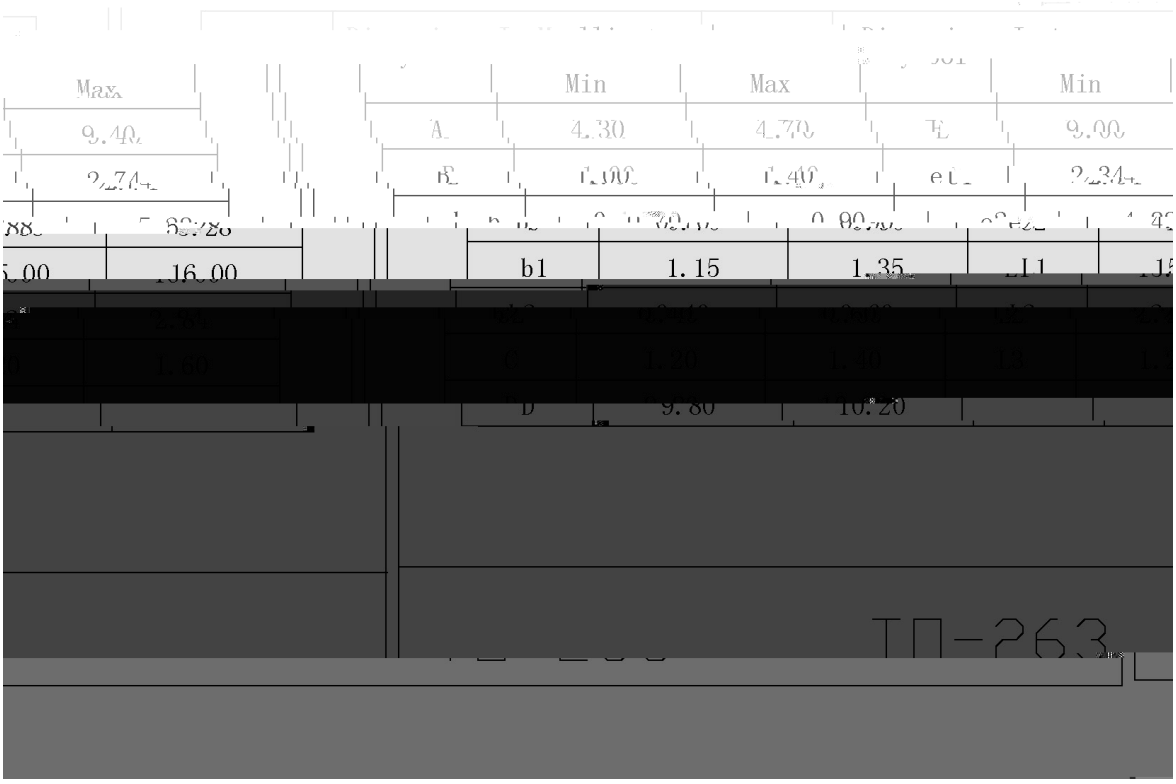
IR - VR



CJ - VR




D
A
4
E
L3
L1
2
b1


Max
Min
Max
Min
9.40
A
4.30
4.70
E
9.00
2.74
B
1.00
1.40
e1
2.34
16.00
b1
1.15
1.35
L1
1.60
C
1.20
1.40
D
9.80
10.20
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